

3 FILES SEARCHED...
6 FILES SEARCHED...
L2 401 L1 AND (SURFACE OR SUBSTRATE)

=> s 12 and (melt or heat) (p)distortion
L3 6 L2 AND (MELT OR HEAT) (P) DISTORTION

=> s (12 or 13) and (Antibacterial or microbiocid? or antimicrobial or silver)
L4 77 (L2 OR L3) AND (ANTIBACTERIAL OR MICROBIOCID? OR ANTIMICROBIAL
OR SILVER)

=> s (11 or 12 or 13 or 14) and bath(4p) (pH or basic or caustic)
L5 28 (L1 OR L2 OR L3 OR L4) AND BATH(4P) (PH OR BASIC OR CAUSTIC)

=> s (11-15) and Klebsiella
L6 0 ((L1 OR L2 OR L3 OR L4 OR L5)) AND KLEBSIELLA

=> s (11 or 12) and klebsiella
L7 0 (L1 OR L2) AND KLEBSIELLA

=> s (11-5) and modified plate
4 FILES SEARCHED...
L8 0 ((L1 OR L2 OR L3 OR L4 OR L5)) AND MODIFIED PLATE

=> dup rem 15
PROCESSING COMPLETED FOR L5
L9 28 DUP REM L5 (0 DUPLICATES REMOVED)

=> d 13 1-6

L3 ANSWER 1 OF 6 USPATFULL
AN 2002:256840 USPATFULL
TI Lamp utilizing fiber for enhanced starting field
IN Golkowski, Czeslaw, Ithaca, NY, UNITED STATES
Hammer, David, Ithaca, NY, UNITED STATES
Song, Byungmoo, Ithaca, NY, UNITED STATES
Tian, Yonglai, Fairfax, VA, UNITED STATES
Cekic, Miodrag, Bethesda, MD, UNITED STATES
Ury, Michael G., Great Barrington, MA, UNITED STATES
Kirkpatrick, Douglas A., Great Falls, VA, UNITED STATES
PI US 2002140381 A1 20021003
AI US 2001-838234 A1 20010420 (9)
PRAI US 2000-199810P 20000426 (60)
DT Utility
FS APPLICATION
LN.CNT 1083
INCL INCLM: 315/363.000
NCL NCLM: 315/363.000
IC [7]
ICM: H05B041-16

L3 ANSWER 2 OF 6 USPATFULL
AN 93:65190 USPATFULL
TI Process for producing a minute-patterned substrate
IN Matsuno, Yoshihiro, Tsukuba, Japan
Matsuda, Atsunori, Tsukuba, Japan
Katayama, Shinya, Tsukuba, Japan
PA Nippon Sheet Glass Co., Ltd., Osaka, Japan (non-U.S. corporation)
PI US 5234717 19930810
AI US 1992-963035 19921019 (7)
RLI Continuation of Ser. No. US 1991-713799, filed on 12 Jun 1991, now
abandoned

PRAI JP 1990-156482 19900614
DT Utility
FS Granted
LN.CNT 785
INCL INCLM: 427/277.000
INCLS: 427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
NCL NCLM: 427/277.000
NCLS: 427/162.000; 427/278.000; 427/294.000; 427/359.000; 427/385.500
IC [5]
ICM: B05D005-00
EXF 427/162; 427/164; 427/165; 427/294; 427/296; 427/385.5; 427/355;
427/277; 427/278; 427/258; 427/359; 427/370; 427/371
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L3 ANSWER 3 OF 6 USPATFULL
AN 93:24745 USPATFULL
TI Process for making sol-gel deposited ferroelectric thin films
insensitive to their substrates
IN Swartz, Scott L., Dublin, OH, United States
Melling, Peter J., Worthington, OH, United States
PA Battelle Memorial Institute, Columbus, OH, United States (U.S.
corporation)
PI US 5198269 19930330
AI US 1989-399724 19890828 (7)
RLI Continuation-in-part of Ser. No. US 1989-342272, filed on 24 Apr 1989,
now abandoned
DT Utility
FS Granted
LN.CNT 1323
INCL INCLM: 427/226.000
INCLS: 427/126.200; 427/126.300; 427/419.300; 427/419.200; 427/379.000;
427/380.000
NCL NCLM: 427/226.000
NCLS: 427/126.200; 427/126.300; 427/379.000; 427/380.000; 427/419.200;
427/419.300
IC [5]
ICM: B05D003-02
EXF 427/419.3; 427/126.2; 427/126.3; 427/100; 427/62; 427/63; 427/226;
427/419.2; 427/379; 427/380; 505/734; 505/735
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L3 ANSWER 4 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 764992 EUROPATFULL ED 19970421 EW 199713 FS OS
TIEN Thin piezoelectric film element, process for the preparation thereof and
ink jet recording head using thin piezoelectric film element.
TIDE Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
dieses piezoelektrische Duennschichtelement verwendender
Tintenstrahldruckkopf.
TIFR Element a couche mince piezoelectrique, procede de fabrication, et tete
d'enregistrement a jet d'encre utilisant cet element a couche mince
piezoelectrique.
IN Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
Nagano, JP;
Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
PA SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,

JP
 SO Wila-EPZ-1997-H13-T2b
 DS R DE; R FR; R GB; R IT
 PIT EPA1 EUROPÄISCHE PATENTANMELDUNG
 PI EP 764992 A1 19970326
 OD 19970326
 AI EP 1996-114974 19960918
 PRAI JP 1995-240372 19950919
 JP 1995-322670 19951212
 JP 1996-190848 19960719
 JP 1996-245353 19960917
 IC ICM H01L041-09
 ICS H01L041-24 B41J002-045

GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE

AN 764992 EUROPATFULL UP 20000903 EW 200034 FS PS
 TIEN Thin piezoelectric film element, process for the preparation thereof and
 ink jet recording head using thin piezoelectric film element.
 TIDE Piezoelektrisches Duennschichtelement, Verfahren zum Herstellen und
 dieses piezoelektrisches Duennschichtelement verwendender
 Tintenstrahldruckkopf.
 TIFR Element a couche mince piezoelectrique, procede de fabrication, et tete
 d'enregistrement a jet d'encre utilisant cet element a couche mince
 piezoelectrique.
 IN Shimada, Masato, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Takahashi, Tetsushi, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Kamei, Hiroyuki, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi,
 Nagano, JP;
 Qui, Hong, c/o Seiko Epson Corp., 3-5, Owa 3-chome, Suwa-shi, Nagano, JP
 PA SEIKO EPSON CORPORATION, 4-1, Nishishinjuku 2-chome, Shinjuku-ku Tokyo,
 JP
 SO Wila-EPS-2000-H34-T2
 DS R DE; R FR; R GB; R IT
 PIT EPB1 EUROPÄISCHE PATENTSCHRIFT
 PI EP 764992 B1 20000823
 OD 19970326
 AI EP 1996-114974 19960918
 PRAI JP 1995-240372 19950919
 JP 1995-322670 19951212
 JP 1996-190848 19960719
 JP 1996-245353 19960917
 REP EP 656665 A US 5198269 A
 REN VASSANT KUMAR ET AL.: "Lead zirconate titanate films by rapid thermal
 processing", APPLIED PHYSICS LETTERS,, 18. March 1991, vol. 58, no. 11,
 pages 1161 to 1163
 IC ICM H01L041-09
 ICS H01L041-24 B41J002-045

L3 ANSWER 5 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 659910 EUROPATFULL ED 19991205 EW 199526 FS OS STA B
 TIEN Semiconductor device and method of fabricating the same.
 TIDE Halbleiter-Vorrichtung und Verfahren zu deren Herstellung.
 TIFR Dispositif semi-conducteur et procede pour fabriquer celui-ci.
 IN Shiindo, Masahiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Kosaka, Daisuke, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,

Suita-shi, Osaka-fu, JP;
 Hikawa, Tetsuo, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Takata, Akira, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Ukai, Yukihiro, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Sawada, Takashi, c/o Mega Chips Corporation, 1-12-38, Esaka-cho,
 Suita-shi, Osaka-fu, JP;
 Asakawa, Toshifumi, 6-9-25, Tsukimino, Yamatoshi, Kanagawa, JP
 PA MEGA CHIPS CORPORATION, 1-12-38, Esaka-cho, Suita-shi, Osaka-fu, JP;
 Crystal Device Corporation, 15-16, Machikaneyama-cho, Toyonaka-shi,
 Osaka-fu, JP
 SO Wila-EPZ-1995-H26-T1a
 DS R DE; R FR; R GB; R NL
 PIT EPA2 EUROPÄISCHE PATENTANMELDUNG
 PI EP 659910 A2 19950628
 OD 19950628
 AI EP 1994-118223 19941118
 PRAI JP 1993-314147 19931119
 JP 1993-314470 19931119
 JP 1993-316108 19931122
 JP 1993-341322 19931210
 JP 1993-345314 19931220
 JP 1993-350297 19931227
 JP 1993-354139 19931228
 JP 1994-15505 19940209
 IC ICM C30B025-00
 ICS C23C016-48

L3 ANSWER 6 OF 6 EUROPATFULL COPYRIGHT 2003 WILA

PATENT APPLICATION - PATENTANMELDUNG - DEMANDE DE BREVET

AN 391226 EUROPATFULL ED 20000903 EW 199041 F3 OS STA B
 TIEN Method for manufacturing layer-built material with silicon dioxide film
 containing organic colorant and the layer-built material manufactured
 thereby.
 TIDE Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit
 einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das
 somit erzeugte Produkt.
 TIFR Procede pour la preparation d'un materiel stratifie avec un film de
 silice contenant un colorant organique et le materiel stratifie ainsi
 produit.
 IN Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP;
 Ino, Juichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP;
 Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP;
 Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken,
 JP
 PA NIPPON SHEET GLASS CO. LTD., 5-11, Dosho-machi 3-chome, Chuo-ku
 Osaka-shi Osaka, JP
 SO Wila-EPZ-1990-H41-T1
 DS R DE; R FR; R GB; R IT; R NL
 PIT EPA1 EUROPÄISCHE PATENTANMELDUNG
 PI EP 391226 A1 19901010
 OD 19901010
 AI EP 1990-105873 19900328
 PRAI JP 1989-83816 19890401
 JP 1989-167366 19890629
 JP 1989-167367 19890629
 JP 1989-167368 19890629
 JP 1989-204214 19890807

JP 1989-217124	19890823		
JP 1989-218054	19890824		
JP 1989-229694	19890905		
JP 1989-238295	19890913		
JP 1989-238296	19890913		
IC ICM C03C017-25			
IC S C03C017-36	G02B001-10	H01J001-64	H01J029-22
	C09D001-04		

GRANTED PATENT - ERTEILTES PATENT - BREVET DELIVRE

AN 391226	EUROPATFULL UP 20011005 EW 199428 FS PS STA B
TIEN	Method for manufacturing layer-built material with silicon dioxide film containing organic colorant and the layer-built material manufactured thereby.
TIDE	Verfahren zur Herstellung eines schichtfoermig aufgebauten Materials mit einem organischen Farbstoff enthaltenden Siliziumdioxidfilm sowie das somit erzeugte Produkt.
TIFR	Procede pour la preparation d'un materiel stratifie avec un film de silice contenant un colorant organique et le materiel stratifie ainsi produit.
IN	Takemura, Kazuo, 12-18, Nogami 6-chome, Takarazuka-shi, Hyogo-ken, JP; Ino, Jyuichi, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP; Kawahara, Hideo, 8-2-312 Makiochi 5-chome, Mino-shi, Osaka-fu, JP; Kitaoka, Masaki, 18-11, Danjo-cho 6-chome, Nishinomiya-shi, Hyogo-ken, JP
PA	NIPPON SHEET GLASS CO. LTD., 5-11, Doshomachi 3-chome, Chuo-ku Osaka-shi Osaka-fu, JP
SO	Wila-EPS-1994-H28-T1
DS	R DE; R FR; R GB; R IT; R NL
PIT	EPB1 EUROPAEISCHE PATENTSCHRIFT
PI	EP 391226 B1 19940713
OD	19901010
AI	EP 1990-105873 19900328
PRAI	JP 1989-83816 19890401
	JP 1989-167366 19890629
	JP 1989-167367 19890629
	JP 1989-167368 19890629
	JP 1989-204214 19890807
	JP 1989-217124 19890823
	JP 1989-218054 19890824
	JP 1989-229694 19890905
	JP 1989-238295 19890913
	JP 1989-238296 19890913
REP	GB 626810 A GB 2018621 A
REN	D. AVNIR, V. KAUFMAN and R. REISFELD, J. Noncryst. Solids 74 (1985), 395 - 406. T. TANI, Ceramics 21 (1986), No. 2, 111 - 118. PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 11, no. 141, May 8, 1987 THE PATENT OFFICE JAPANESE GOVERNMENT page 76 C 421 PATENT ABSTRACTS OF JAPAN, unexamined applications, C field, vol. 10, no. 23, January 29, 1986 THE PATENT OFFICE JAPANESE GOVERNMENT page 96 C 325
IC	ICM C03C017-25
	IC S C03C017-36 G02B001-10 H01J001-64 H01J029-22
	C09D001-04

=>

L5 ANSWER 5 OF 28 USPATFULL
AN 2002:10777 USPATFULL
TI Nanoparticulate titania dioxide coatings, and processes for the
IN production and use thereof
PI US 2002005145 AI 20020117
AI US 2000-736738 AI 20001213 (9)
PRAI US 2000-216937P 20000710 (60)
US 2000-202033P 20000505 (60)
US 2000-188761P 20000313 (60)
US 1999-170509P 19991213 (60)
DT UTILITY
IN.CNT 2102 APPLICATION
INC1 INCIM: 106/436.000
INC2 NCIM: 106/436.000
IC [7] ICM: C09C001-36
EXF 435/7.93; 435/26; 435/28; 435/176; 436/527; 436/815; 436/829
CAS INDEXING IS AVAILABLE FOR THIS PATENT.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

IC [7] ICM: C09C001-36
INC1 INCIM: 106/436.000
INC2 NCIM: 106/436.000
IN.CNT 2102 APPLICATION
ES UTILITY
PRAI US 2000-736738 AI 20001213 (9)
US 2000-216937P 20000710 (60)
US 2000-202033P 20000505 (60)
US 2000-188761P 20000313 (60)
US 1999-170509P 19991213 (60)
DT UTILITY
IN.CNT 2102 APPLICATION
INC1 INCIM: 106/436.000
INC2 NCIM: 106/436.000
IC [7] ICM: C09C001-36
EXF 435/7.93; 435/26; 435/28; 435/176; 436/527; 436/815; 436/829
CAS INDEXING IS AVAILABLE FOR THIS PATENT.